

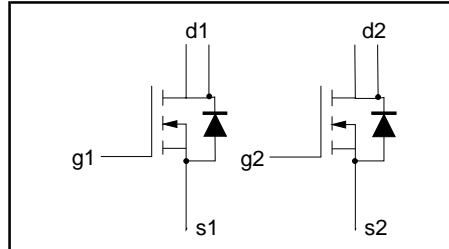
Dual N-channel TrenchMOS™ transistor

PHKD3NQ10T

FEATURES

- Dual device
- Low on-state resistance
- Fast switching
- Low profile surface mount package

SYMBOL



QUICK REFERENCE DATA

$V_{DS} = 100\text{ V}$
$I_D = 3\text{ A}$
$R_{DS(ON)} \leq 90\text{ m}\Omega (V_{GS} = 10\text{ V})$

GENERAL DESCRIPTION

Dual N-channel enhancement mode field-effect transistor in a plastic envelope using 'trench' technology.

Applications:-

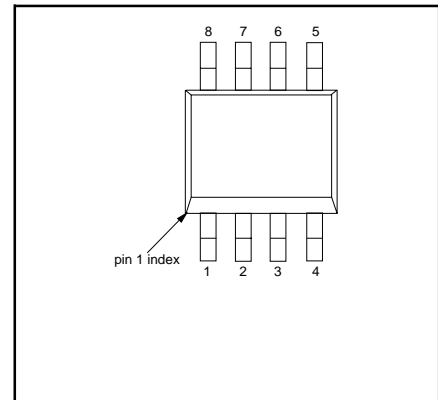
- Motor and relay drivers
- d.c. to d.c. converters

The PHKD3NQ10T is supplied in the SOT96-1 (SO8) surface mounting package.

PINNING

PIN	DESCRIPTION
1	source 1
2	gate 1
3	source 2
4	gate 2
5,6	drain 2
7,8	drain 1

SOT96-1



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{DS}	Continuous drain-source voltage	$T_j = 25\text{ }^\circ\text{C}$ to $150\text{ }^\circ\text{C}$	-	100	V
V_{DGR}	Drain-gate voltage	$T_j = 25\text{ }^\circ\text{C}$ to $150\text{ }^\circ\text{C}$; $R_{GS} = 20\text{ k}\Omega$	-	100	V
V_{GS}	Gate-source voltage		-	± 20	V
I_D	Drain current per MOSFET	$T_a = 25\text{ }^\circ\text{C}$, $t \leq 10\text{ s}$	-	3	A
		$T_a = 70\text{ }^\circ\text{C}$, $t \leq 10\text{ s}$	-	2.4	A
I_D	Drain current per MOSFET (both MOSFETs conducting)	$T_a = 25\text{ }^\circ\text{C}$, $t \leq 10\text{ s}$	-	2.2	A
		$T_a = 70\text{ }^\circ\text{C}$, $t \leq 10\text{ s}$	-	1.7	A
I_{DM}	Drain current (pulse peak value per MOSFET)	$T_a = 25\text{ }^\circ\text{C}$	-	12	A
P_{tot}	Total power dissipation	$T_a = 25\text{ }^\circ\text{C}$, $t \leq 10\text{ s}$	-	2	W
		$T_a = 70\text{ }^\circ\text{C}$, $t \leq 10\text{ s}$	-	1.3	W
T_{stg} , T_j	Storage & operating temperature		- 65	150	$^\circ\text{C}$

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$R_{th\ j-a}$	Thermal resistance junction to ambient	Surface mounted on FR4 board, $t \leq 10\text{ sec}$; either or both MOSFETs conducting	-	62.5	K/W
$R_{th\ j-a}$	Thermal resistance junction to ambient	Surface mounted on FR4 board; either or both MOSFETs conducting	150	-	K/W

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ELECTRICAL CHARACTERISTICS $T_j = 25^\circ\text{C}$, per MOSFET unless otherwise specified

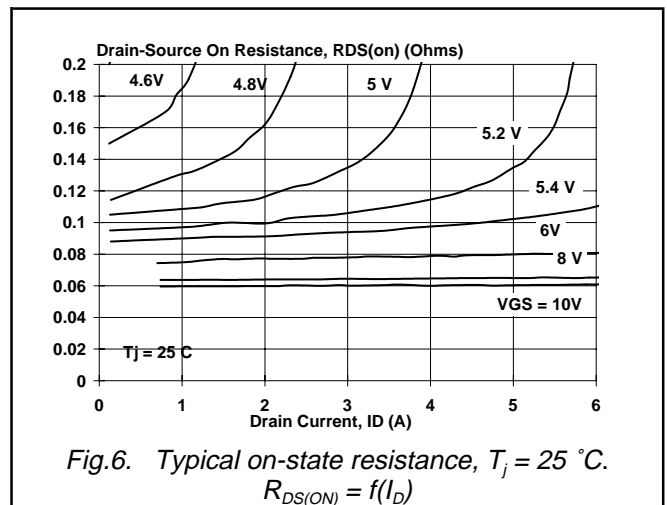
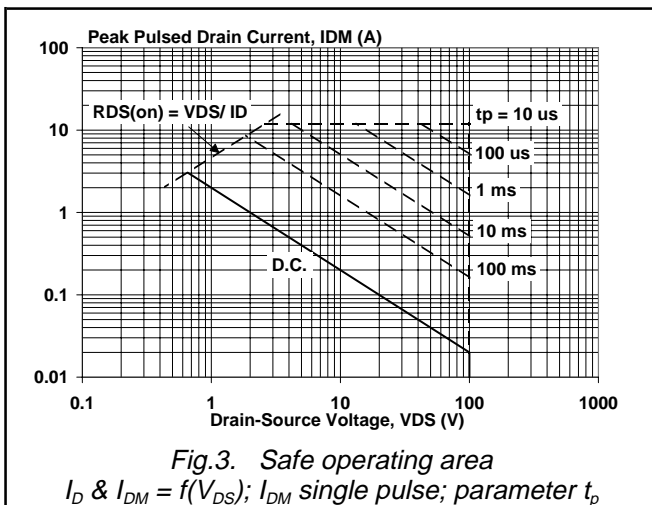
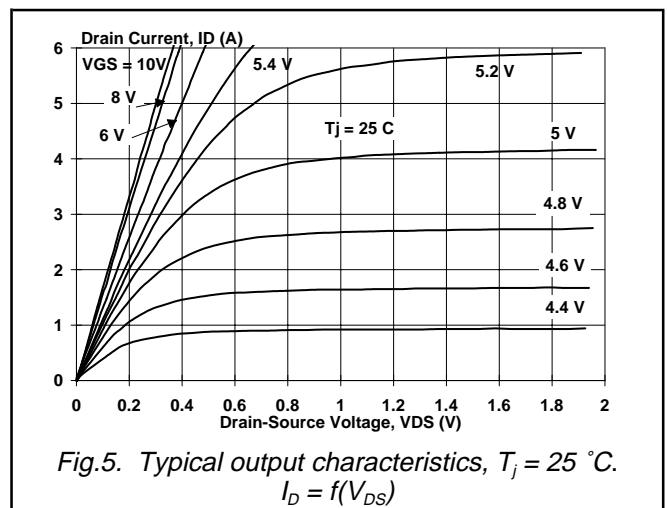
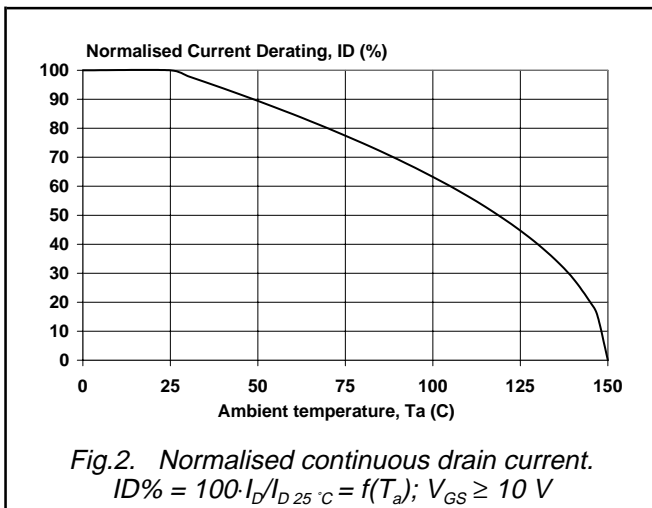
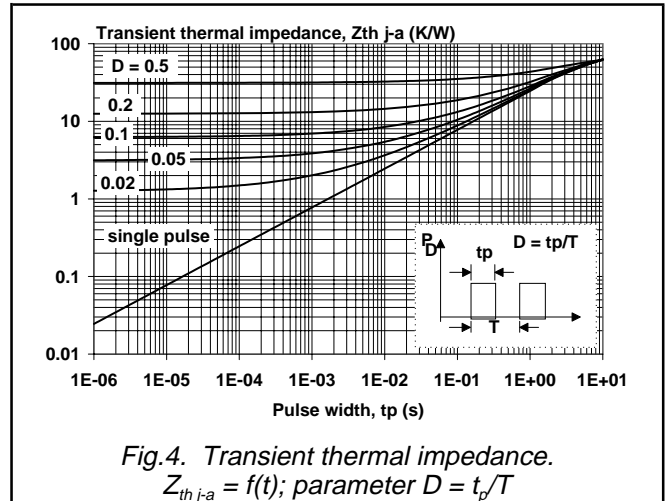
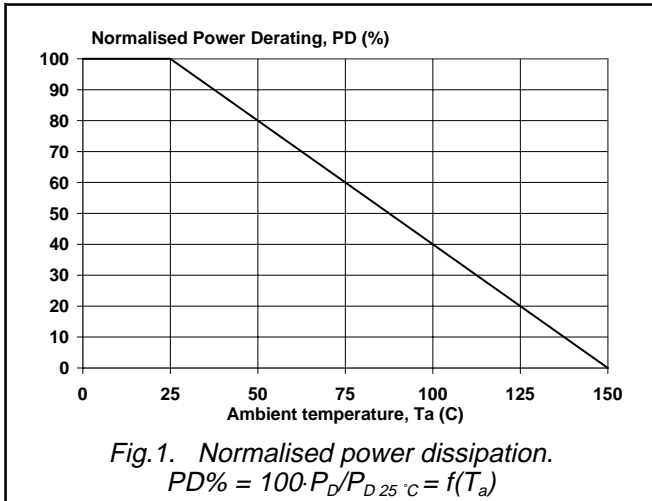
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}; I_D = 250\ \mu\text{A};$ $T_j = -55^\circ\text{C}$	100 89	- -	- -	V V
$V_{GS(TO)}$	Gate threshold voltage	$V_{DS} = V_{GS}; I_D = 1\ \text{mA}$ $T_j = 150^\circ\text{C}$ $T_j = -55^\circ\text{C}$	2 1.1 -	3 -	4 - 6	V V V
$R_{DS(ON)}$	Drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 1.5\ \text{A}$ $T_j = 150^\circ\text{C}$	- -	70 -	90 216	m Ω m Ω
I_{GSS}	Gate source leakage current	$V_{GS} = \pm 20\text{ V}; V_{DS} = 0\ \text{V}$	-	10	100	nA
I_{DSS}	Zero gate voltage drain current	$V_{DS} = 100\text{ V}; V_{GS} = 0\ \text{V};$ $T_j = 150^\circ\text{C}$	-	0.05	10 100	μA μA
$Q_{g(\text{tot})}$	Total gate charge	$I_D = 3\ \text{A}; V_{DD} = 80\ \text{V}; V_{GS} = 10\ \text{V}$	-	21	-	nC
Q_{gs}	Gate-source charge		-	2.5	-	nC
Q_{gd}	Gate-drain (Miller) charge		-	8	-	nC
$t_{d\text{ on}}$	Turn-on delay time	$V_{DD} = 50\ \text{V}; R_D = 15\ \Omega;$	-	6	-	ns
t_r	Turn-on rise time	$V_{GS} = 10\ \text{V}; R_G = 5.6\ \Omega$	-	12	-	ns
$t_{d\text{ off}}$	Turn-off delay time	Resistive load	-	20	-	ns
t_f	Turn-off fall time		-	10	-	ns
L_d	Internal drain inductance	Measured from drain lead to centre of die	-	2.5	-	nH
L_s	Internal source inductance	Measured from source lead to source bond pad	-	5	-	nH
C_{iss}	Input capacitance	$V_{GS} = 0\ \text{V}; V_{DS} = 20\ \text{V}; f = 1\ \text{MHz}$	-	633	-	pF
C_{oss}	Output capacitance		-	103	-	pF
C_{rss}	Feedback capacitance		-	61	-	pF

REVERSE DIODE LIMITING VALUES AND CHARACTERISTICS $T_j = 25^\circ\text{C}$, per MOSFET unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_S	Continuous source diode current	$T_a = 25^\circ\text{C}, t \leq 10\ \text{s}$	-	-	2	A
I_{SM}	Pulsed source diode current		-	-	12	A
V_{SD}	Diode forward voltage	$I_F = 2\ \text{A}; V_{GS} = 0\ \text{V}$	-	0.8	1.2	V
t_{rr}	Reverse recovery time	$I_F = 2\ \text{A}; -di_F/dt = 100\ \text{A}/\mu\text{s};$	-	55	-	ns
Q_{rr}	Reverse recovery charge	$V_{GS} = 0\ \text{V}; V_R = 25\ \text{V}$	-	135	-	nC

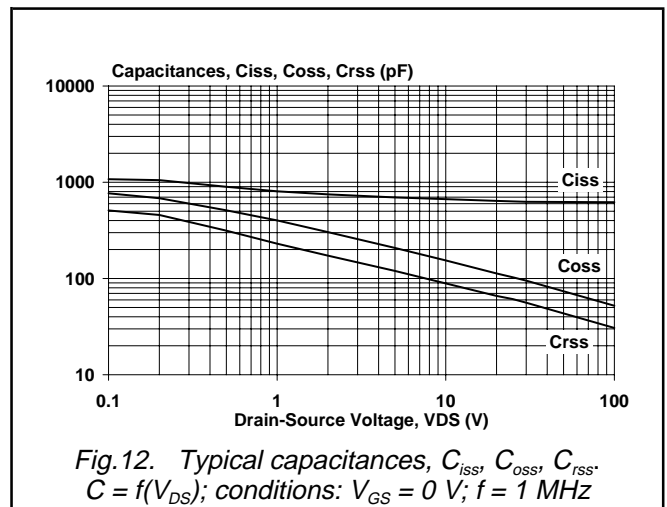
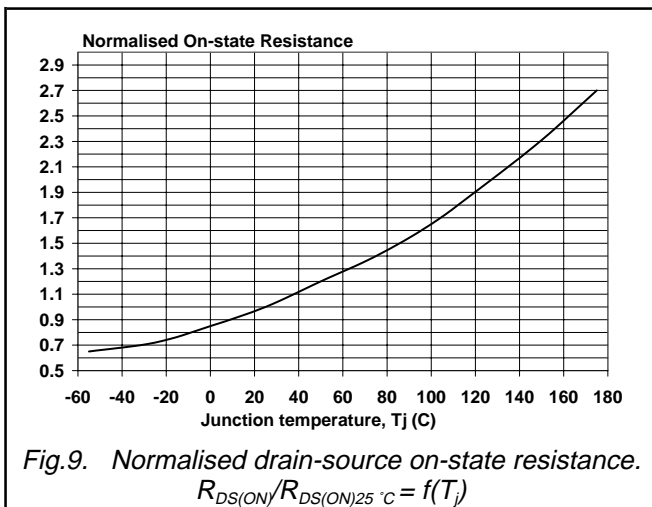
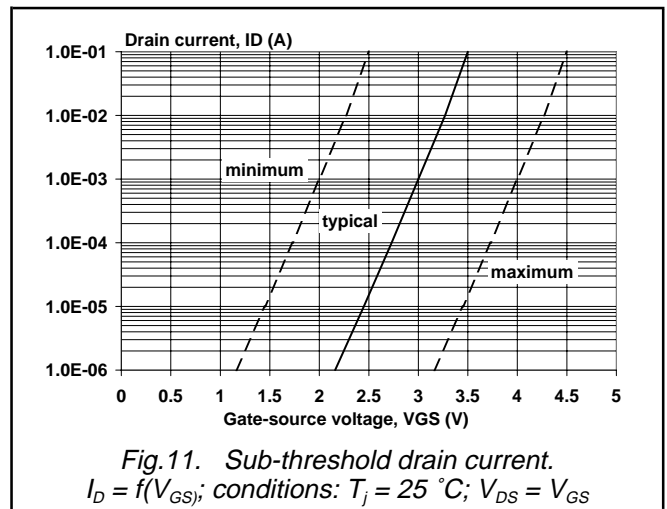
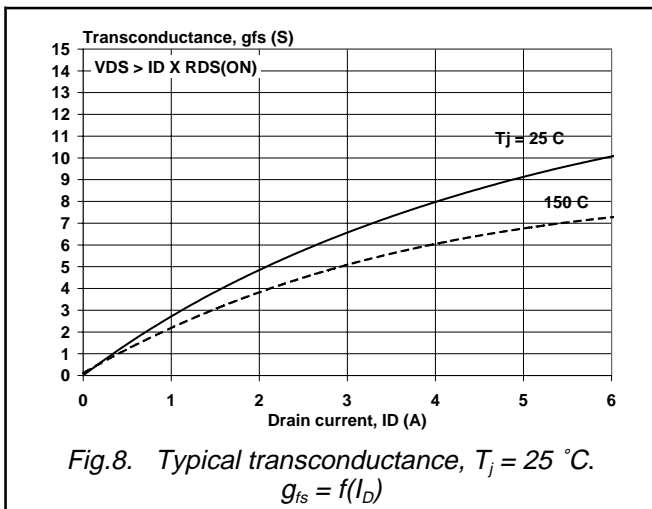
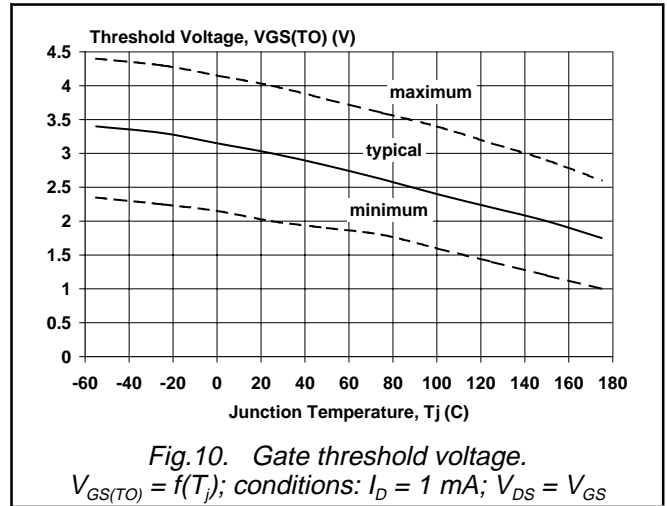
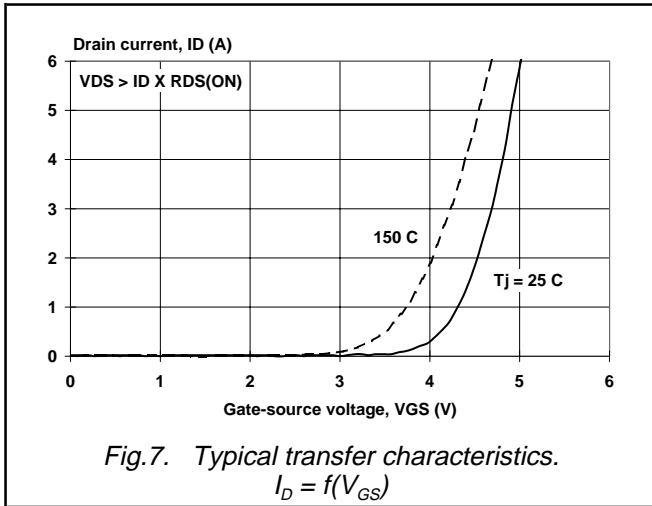
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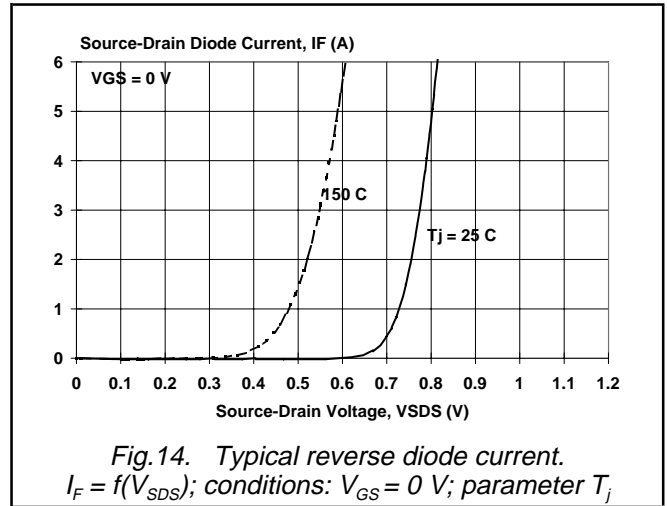
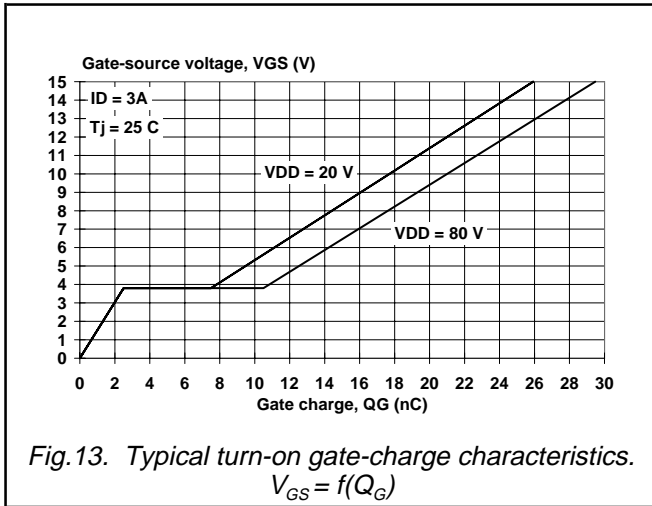
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MECHANICAL DATA

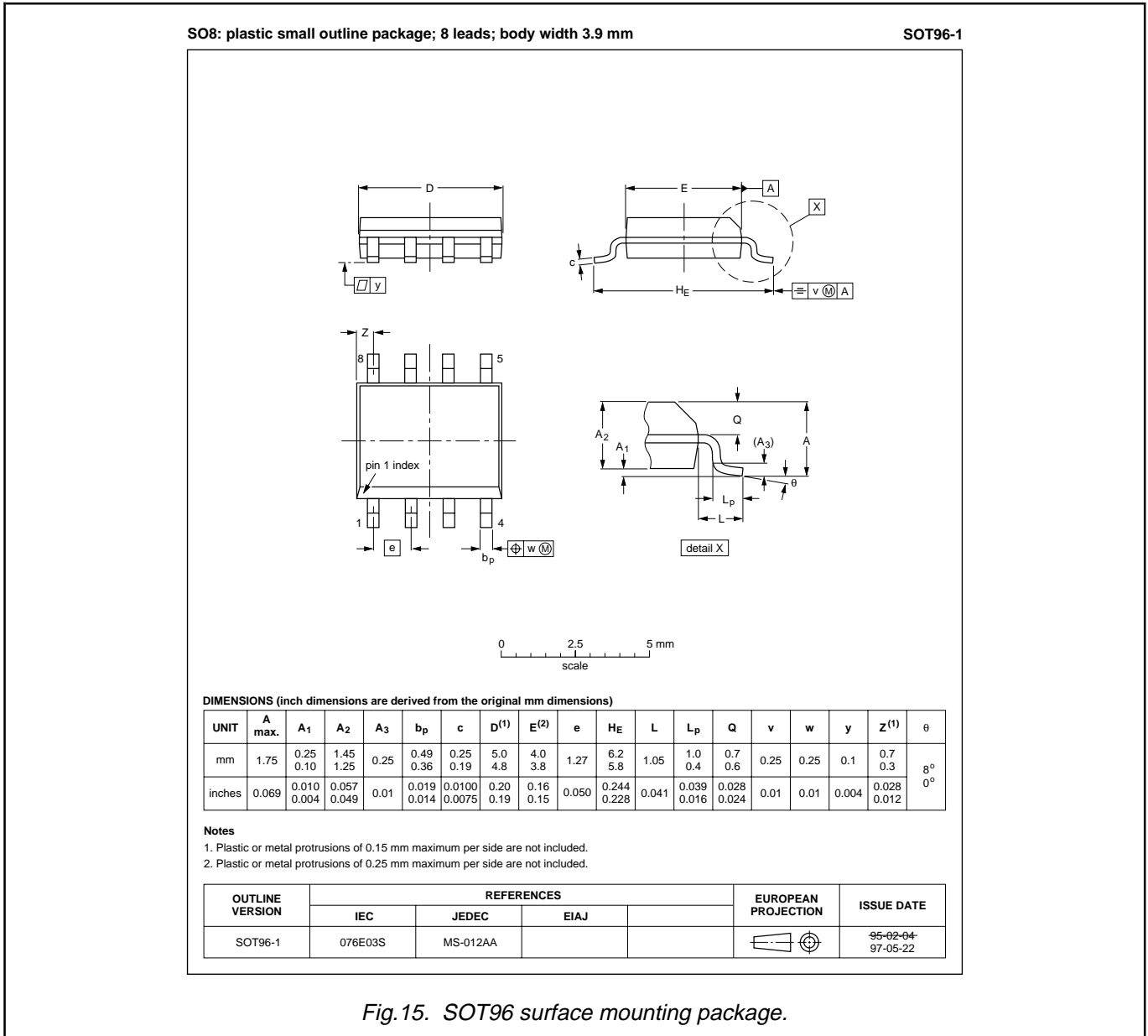


Fig. 15. SOT96 surface mounting package.

Notes

1. This product is supplied in anti-static packaging. The gate-source input must be protected against static discharge during transport or handling.
2. Refer to Integrated Circuit Packages, Data Handbook IC26.
3. Epoxy meets UL94 V0 at 1/8".

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DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	
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